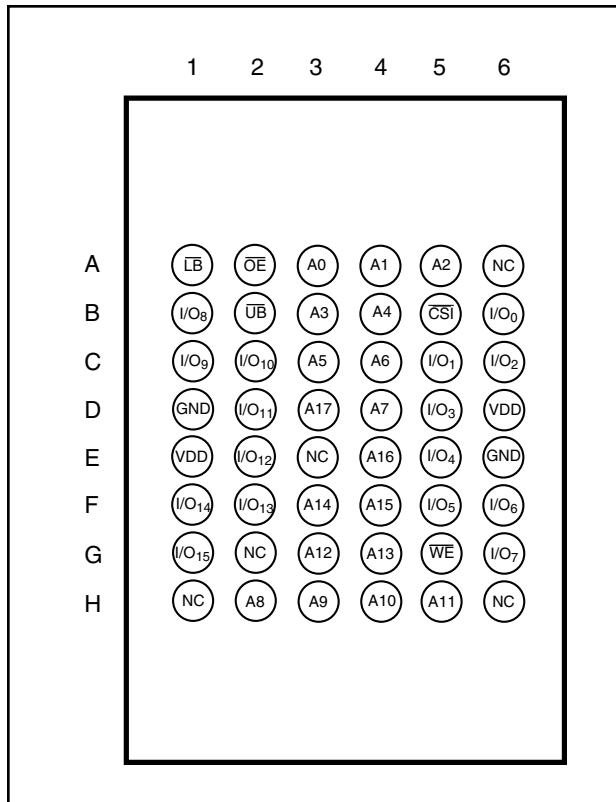
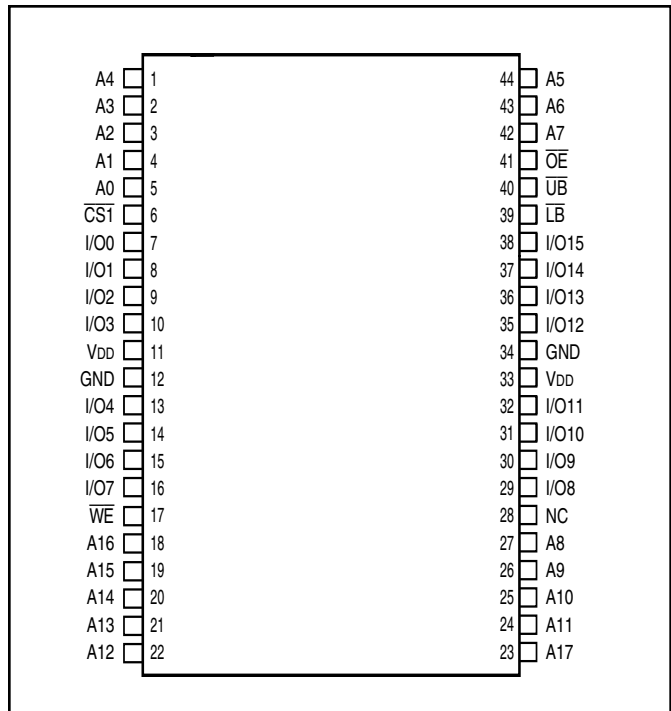


PIN CONFIGURATIONS

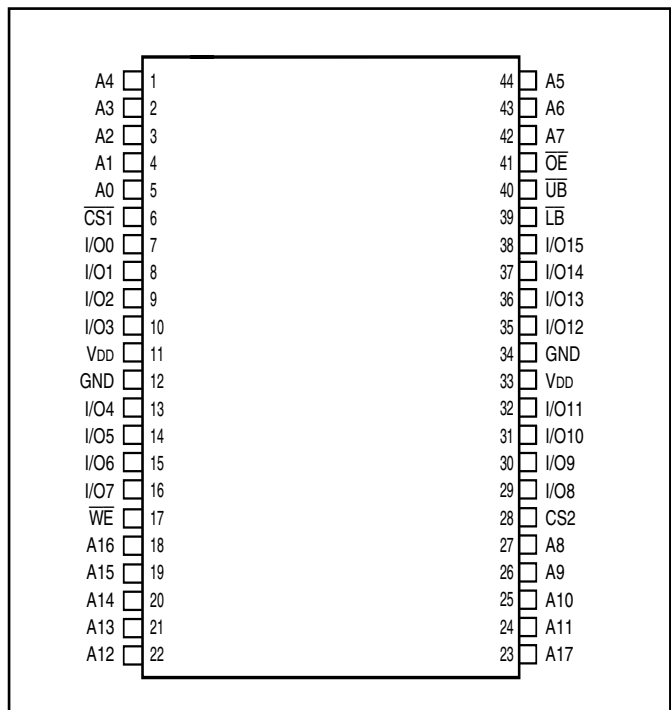
48- ball mini BGA (6mm x 8mm)
(Package Code B)



44-Pin mini TSOP (Type II)
(Package Code T)



44-Pin mini TSOP (Type II)
2 Chip Enable Option
(Package Code T2)



PIN DESCRIPTIONS

A0-A17	Address Inputs
I/O0-I/O15	Data Inputs/Outputs
CS1, CS2	Chip Enable Input
OE	Output Enable Input
WE	Write Enable Input
LB	Lower-byte Control (I/O0-I/O7)
UB	Upper-byte Control (I/O8-I/O15)
NC	No Connection
VDD	Power
GND	Ground

TRUTH TABLE

Mode	$\overline{WE}$	$\overline{CS1}$	$\overline{OE}$	$\overline{LB}$	$\overline{UB}$	I/O PIN		V_{DD} Current
						I/O0-I/O7	I/O8-I/O15	
Not Selected	X	H	X	X	X	High-Z	High-Z	IsB1, IsB2
	X	X	X	H	H	High-Z	High-Z	IsB1, IsB2
Output Disabled	H	L	H	L	X	High-Z	High-Z	Icc
	H	L	H	X	L	High-Z	High-Z	Icc
Read	H	L	L	L	H	DOUT	High-Z	Icc
	H	L	L	H	L	High-Z	DOUT	
	H	L	L	L	L	DOUT	DOUT	
Write	L	L	X	L	H	DIN	High-Z	Icc
	L	L	X	H	L	High-Z	DIN	
	L	L	X	L	L	DIN	DIN	

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Value	Unit
V_{TERM}	Terminal Voltage with Respect to GND	-0.2 to $V_{DD}+0.3$	V
V_{DD}	V_{DD} Related to GND	-0.2 to $V_{DD}+0.3$	V
T_{STG}	Storage Temperature	-65 to +150	°C
P_T	Power Dissipation	1.0	W

Note:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

OPERATING RANGE (V_{DD})

Range	Ambient Temperature	IS62WV25616ALL	IS62WV25616BLL
Commercial	0°C to +70°C	1.65V - 2.2V	2.5V-3.6V
Industrial	-40°C to +85°C	1.65V - 2.2V	2.5V-3.6V

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	V_{DD}	Min.	Max.	Unit
V_{OH}	Output HIGH Voltage	$I_{OH} = -0.1$ mA	1.65-2.2V	1.4	—	V
		$I_{OH} = -1$ mA	2.5-3.6V	2.2	—	V
V_{OL}	Output LOW Voltage	$I_{OL} = 0.1$ mA	1.65-2.2V	—	0.2	V
		$I_{OL} = 2.1$ mA	2.5-3.6V	—	0.4	V
V_{IH}	Input HIGH Voltage		1.65-2.2V	1.4	$V_{DD} + 0.2$	V
			2.5-3.6V	2.2	$V_{DD} + 0.3$	V
$V_{IL}^{(1)}$	Input LOW Voltage		1.65-2.2V	-0.2	0.4	V
			2.5-3.6V	-0.2	0.8	V
I_{LI}	Input Leakage	$GND \leq V_{IN} \leq V_{DD}$		-1	1	μA
I_{LO}	Output Leakage	$GND \leq V_{OUT} \leq V_{DD}$, Outputs Disabled		-1	1	μA

Notes: 1. V_{IL} (min.) = -1.0V for pulse width less than 10 ns.

IS62WV25616ALL, IS62WV25616BLL

IS62WV25616ALL, POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

Symbol	Parameter	Test Conditions		Max. 70	Unit
I _{CC}	V _{DD} Dynamic Operating Supply Current	V _{DD} = Max., I _{OUT} = 0 mA, f = f _{MAX}	Com. Ind.	25 30	mA
I _{CC1}	Operating Supply Current	V _{DD} = Max., $\overline{CS1} = 0.2V$ $\overline{WE} = V_{DD}-0.2V$ f=1MHz	Com. Ind.	10 10	mA
I _{SB1}	TTL Standby Current (TTL Inputs)	V _{DD} = Max., V _{IN} = V _{IH} or V _{IL} $\overline{CS1} = V_{IH}$, f = 1 MHz OR	Com. Ind.	0.35 0.35	mA
	ULB Control	V _{DD} = Max., V _{IN} = V _{IH} or V _{IL} $\overline{CS1} = V_{IL}$, f = 0, $\overline{UB} = V_{IH}$, $\overline{LB} = V_{IH}$			
I _{SB2}	CMOS Standby Current (CMOS Inputs)	V _{DD} = Max., $\overline{CS1} \geq V_{DD} - 0.2V$, V _{IN} ≥ V _{DD} - 0.2V, or V _{IN} ≤ 0.2V, f = 0 OR	Com. Ind.	15 15	μA
	ULB Control	V _{DD} = Max., $\overline{CS1} = V_{IL}$, V _{IN} ≤ 0.2V, f = 0; $\overline{UB} / \overline{LB} = V_{DD} - 0.2V$			

IS62WV25616BLL, POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

Symbol	Parameter	Test Conditions		Max. 55	Max. 70	Unit
I _{CC}	V _{DD} Dynamic Operating Supply Current	V _{DD} = Max., I _{OUT} = 0 mA, f = f _{MAX}	Com. Ind.	40 45	35 40	mA
I _{CC1}	Operating Supply Current	V _{DD} = Max., $\overline{CS1} = 0.2V$ $\overline{WE} = V_{DD}-0.2V$ f=1MHz	Com. Ind.	15 15	15 15	mA
I _{SB1}	TTL Standby Current (TTL Inputs)	V _{DD} = Max., V _{IN} = V _{IH} or V _{IL} $\overline{CS1} = V_{IH}$, f = 1 MHz OR	Com. Ind.	0.35 0.35	0.35 0.35	mA
	ULB Control	V _{DD} = Max., V _{IN} = V _{IH} or V _{IL} $\overline{CS1} = V_{IL}$, f = 0, $\overline{UB} = V_{IH}$, $\overline{LB} = V_{IH}$				
I _{SB2}	CMOS Standby Current (CMOS Inputs)	V _{DD} = Max., $\overline{CS1} \geq V_{DD} - 0.2V$, V _{IN} ≥ V _{DD} - 0.2V, or V _{IN} ≤ 0.2V, f = 0 OR	Com. Ind. typ. ⁽¹⁾	15 15 3	15 15	μA
	ULB Control	V _{DD} = Max., $\overline{CS1} = V_{IL}$, V _{IN} ≤ 0.2V, f = 0; $\overline{UB} / \overline{LB} = V_{DD} - 0.2V$				

Note:

1. Typical values are measured at V_{DD} = 3.0V, T_A = 25°C. Not 100% tested.

CAPACITANCE⁽¹⁾

Symbol	Parameter	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	8	pF
C _{OUT}	Input/Output Capacitance	V _{OUT} = 0V	10	pF

Note:

1. Tested initially and after any design or process changes that may affect these parameters.

AC TEST CONDITIONS

Parameter	IS62WV25616ALL (Unit)	IS62WV25616BLL (Unit)
Input Pulse Level	0.4V to V _{DD} -0.2V	0.4V to V _{DD} -0.3V
Input Rise and Fall Times	5 ns	5ns
Input and Output Timing and Reference Level	V _{REF}	V _{REF}
Output Load	See Figures 1 and 2	See Figures 1 and 2

	IS62WV25616ALL 1.65V-2.2V	IS62WV25616BLL 2.5V - 3.6V
R1(Ω)	3070	3070
R2(Ω)	3150	3150
V _{REF}	0.9V	1.5V
V _{TM}	1.8V	2.8V

AC TEST LOADS

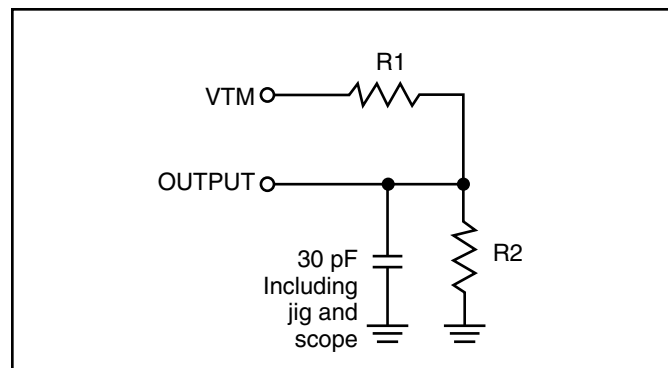


Figure 1

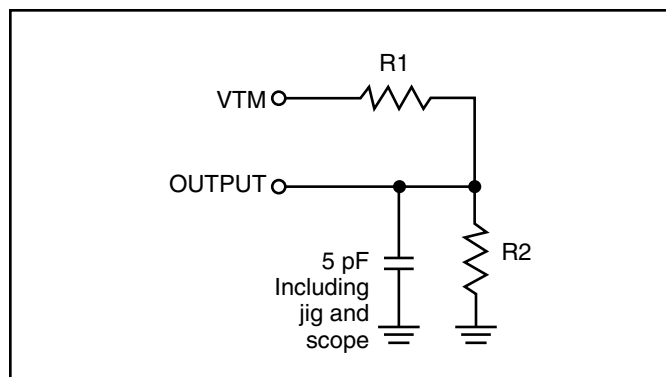


Figure 2

READ CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range)

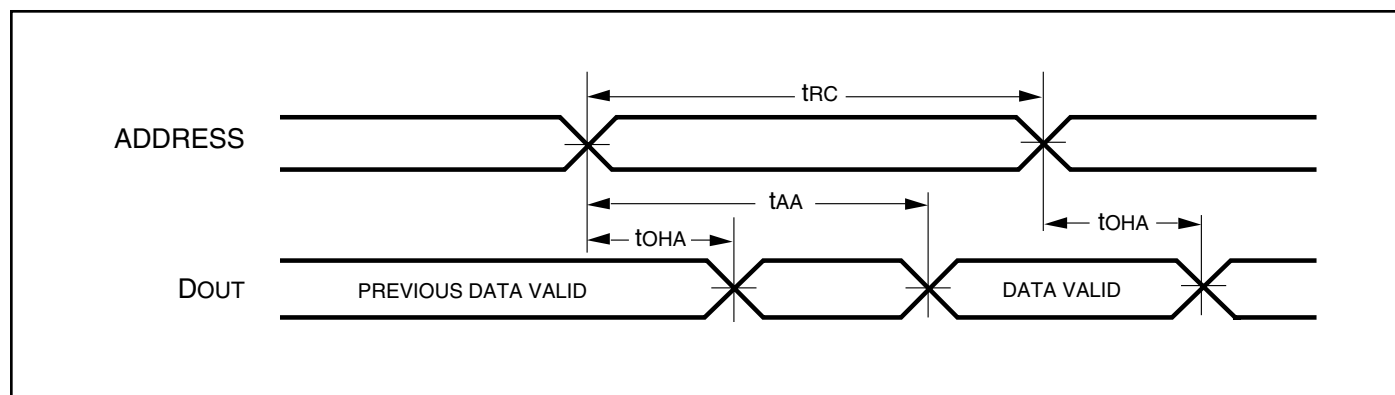
Symbol	Parameter	55 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
t _{RC}	Read Cycle Time	55	—	70	—	ns
t _{AA}	Address Access Time	—	55	—	70	ns
t _{OHA}	Output Hold Time	10	—	10	—	ns
t _{ACS1}	$\overline{\text{CS}}1$ Access Time	—	55	—	70	ns
t _{DOE}	$\overline{\text{OE}}$ Access Time	—	25	—	35	ns
t _{HZOE} ⁽²⁾	$\overline{\text{OE}}$ to High-Z Output	—	20	—	25	ns
t _{LZOE} ⁽²⁾	$\overline{\text{OE}}$ to Low-Z Output	5	—	5	—	ns
t _{HZCS1}	$\overline{\text{CS}}1$ to High-Z Output	0	20	0	25	ns
t _{LZCS1}	$\overline{\text{CS}}1$ to Low-Z Output	10	—	10	—	ns
t _{BA}	$\overline{\text{LB}}, \overline{\text{UB}}$ Access Time	—	55	—	70	ns
t _{HZB}	$\overline{\text{LB}}, \overline{\text{UB}}$ to High-Z Output	0	20	0	25	ns
t _{LZB}	$\overline{\text{LB}}, \overline{\text{UB}}$ to Low-Z Output	0	—	0	—	ns

Notes:

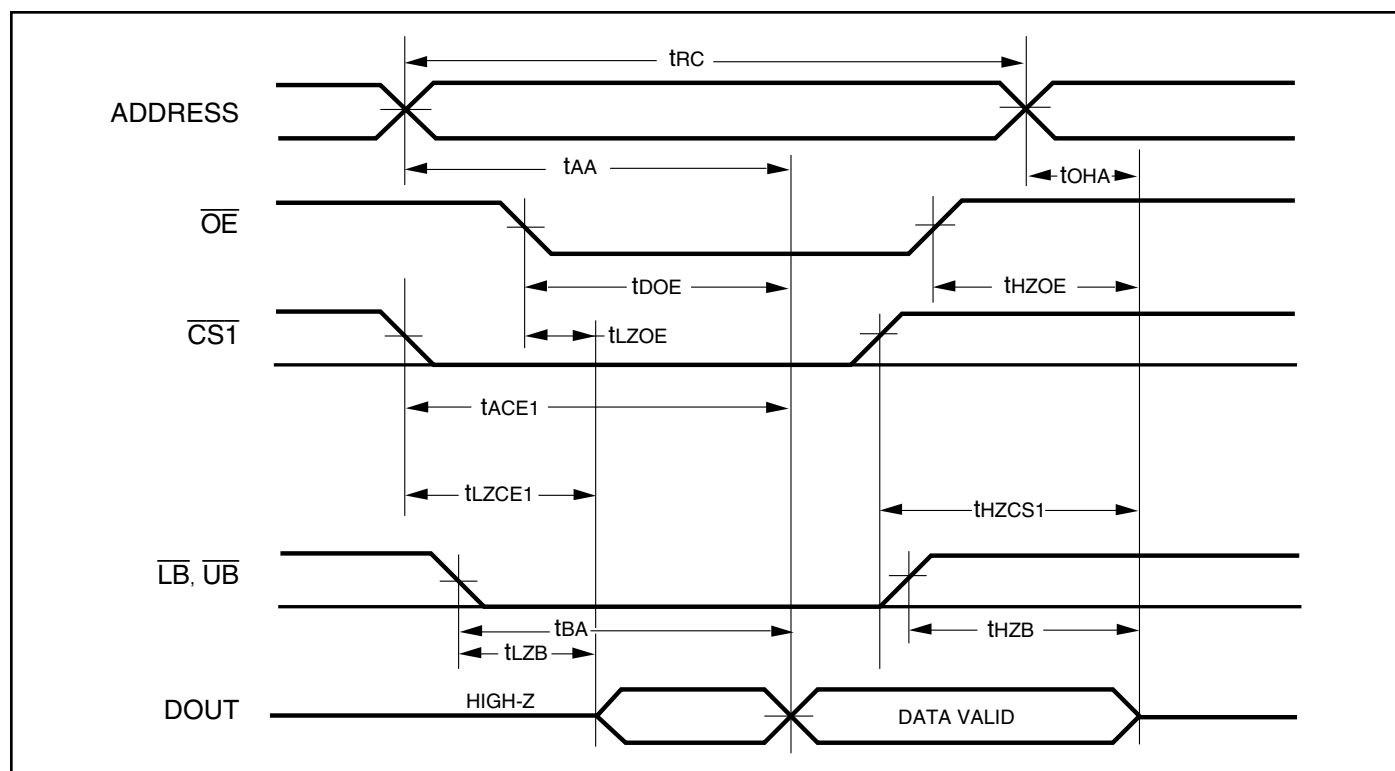
1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V/1.5V, input pulse levels of 0.4 to V_{DD}-0.2V/V_{DD}-0.3V and output loading specified in Figure 1.
2. Tested with the load in Figure 2. Transition is measured ± 500 mV from steady-state voltage. Not 100% tested.

AC WAVEFORMS

READ CYCLE NO. 1^(1,2) (Address Controlled) ($\overline{CS1} = \overline{OE} = V_{IL}$, $\overline{WE} = V_{IH}$, $\overline{UB}$ or $\overline{LB} = V_{IL}$)



READ CYCLE NO. 2^(1,3) ($\overline{CS1}$, $\overline{OE}$, AND $\overline{UB}/\overline{LB}$ Controlled)



Notes:

1. $\overline{WE}$ is HIGH for a Read Cycle.
2. The device is continuously selected. $\overline{OE}$, $\overline{CS1}$, $\overline{UB}$, or $\overline{LB} = V_{IL}$. $\overline{WE} = V_{IH}$.
3. Address is valid prior to or coincident with $\overline{CS1}$ LOW transition.

WRITE CYCLE SWITCHING CHARACTERISTICS^(1,2) (Over Operating Range)

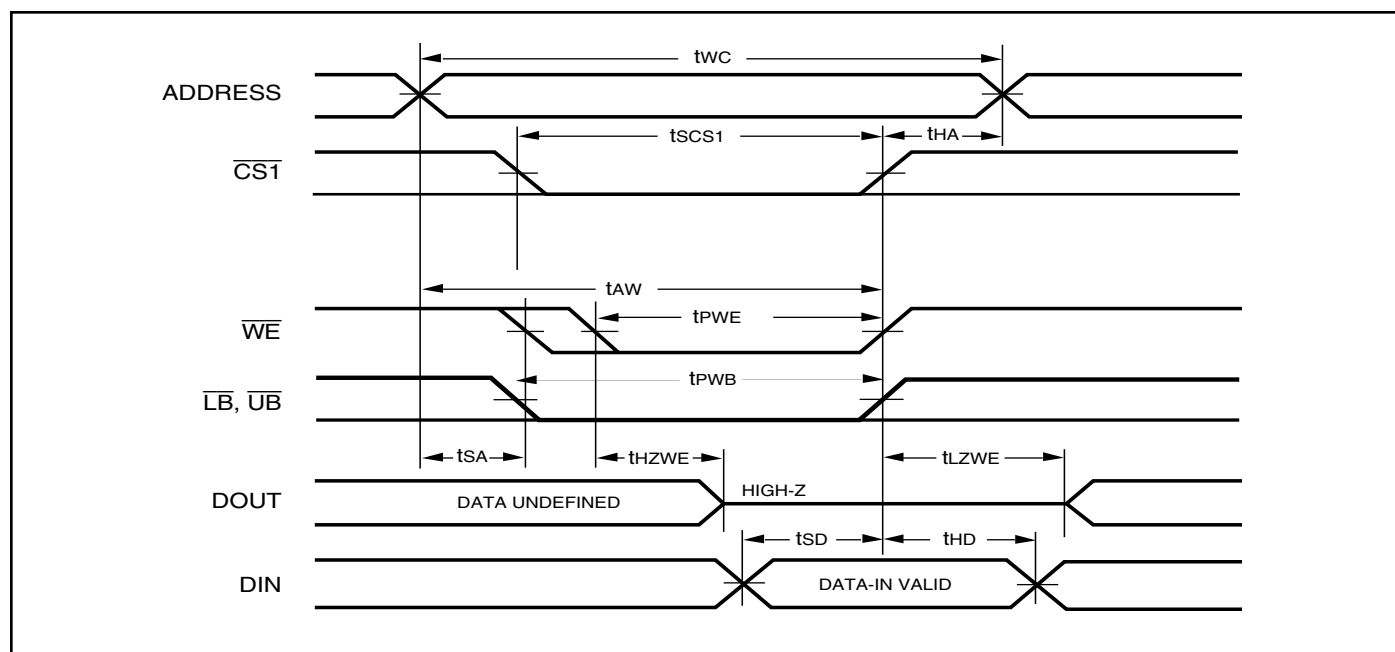
Symbol	Parameter	55 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
t _{wc}	Write Cycle Time	55	—	70	—	ns
t _{scs1}	$\overline{\text{CS1}}$ to Write End	45	—	60	—	ns
t _{aw}	Address Setup Time to Write End	45	—	60	—	ns
t _{ha}	Address Hold from Write End	0	—	0	—	ns
t _{sa}	Address Setup Time	0	—	0	—	ns
t _{pwb}	$\overline{\text{LB}}$, $\overline{\text{UB}}$ Valid to End of Write	45	—	60	—	ns
t _{pwe}	$\overline{\text{WE}}$ Pulse Width	40	—	50	—	ns
t _{sd}	Data Setup to Write End	25	—	30	—	ns
t _{hd}	Data Hold from Write End	0	—	0	—	ns
t _{hzwe} ⁽³⁾	$\overline{\text{WE}}$ LOW to High-Z Output	—	20	—	20	ns
t _{lzwe} ⁽³⁾	$\overline{\text{WE}}$ HIGH to Low-Z Output	5	—	5	—	ns

Notes:

1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V/1.5V, input pulse levels of 0.4V to V_{DD}-0.2V/V_{DD}-0.3V and output loading specified in Figure 1.
2. The internal write time is defined by the overlap of $\overline{\text{CS1}}$ LOW and $\overline{\text{UB}}$ or $\overline{\text{LB}}$, and $\overline{\text{WE}}$ LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.
3. Tested with the load in Figure 2. Transition is measured ± 500 mV from steady-state voltage. Not 100% tested.

AC WAVEFORMS

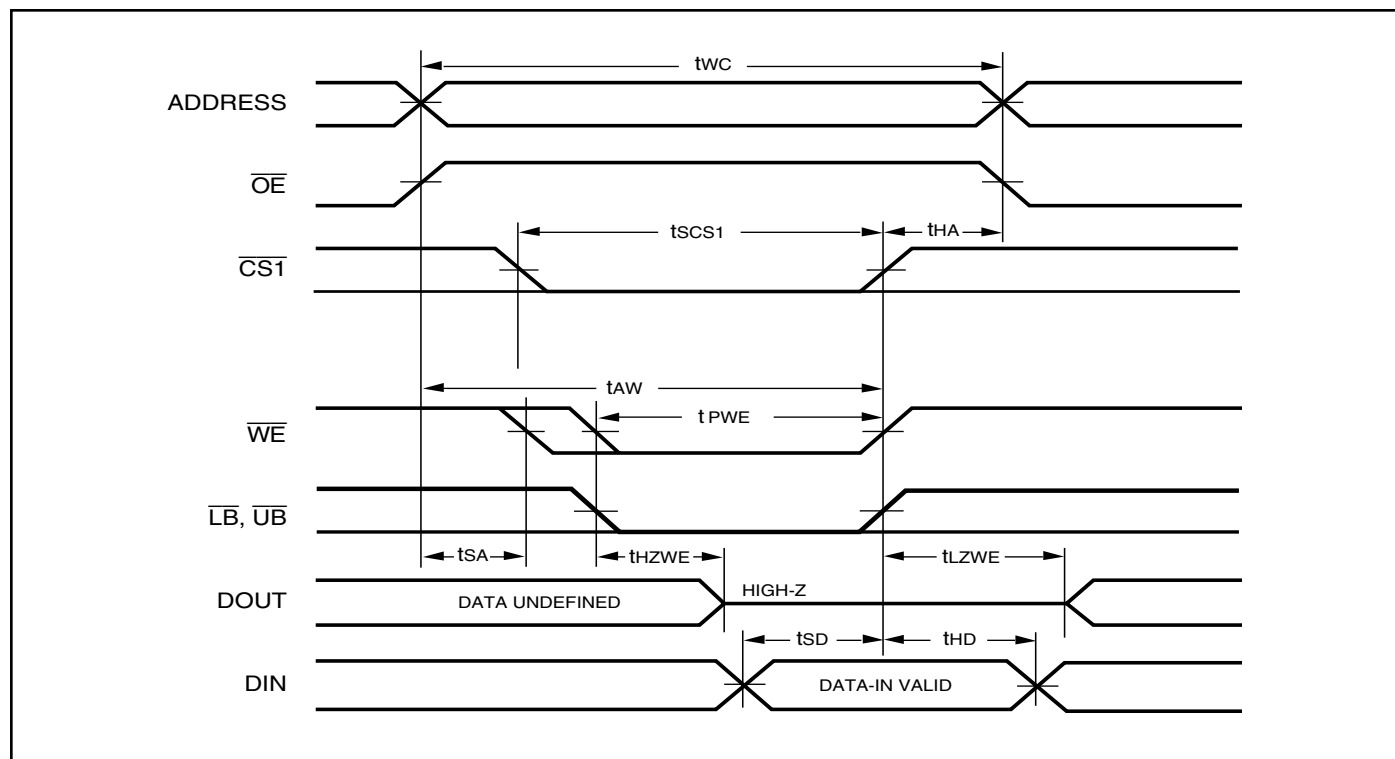
WRITE CYCLE NO. 1^(1,2) ($\overline{CS1}$ Controlled, $\overline{OE}$ = HIGH or LOW)

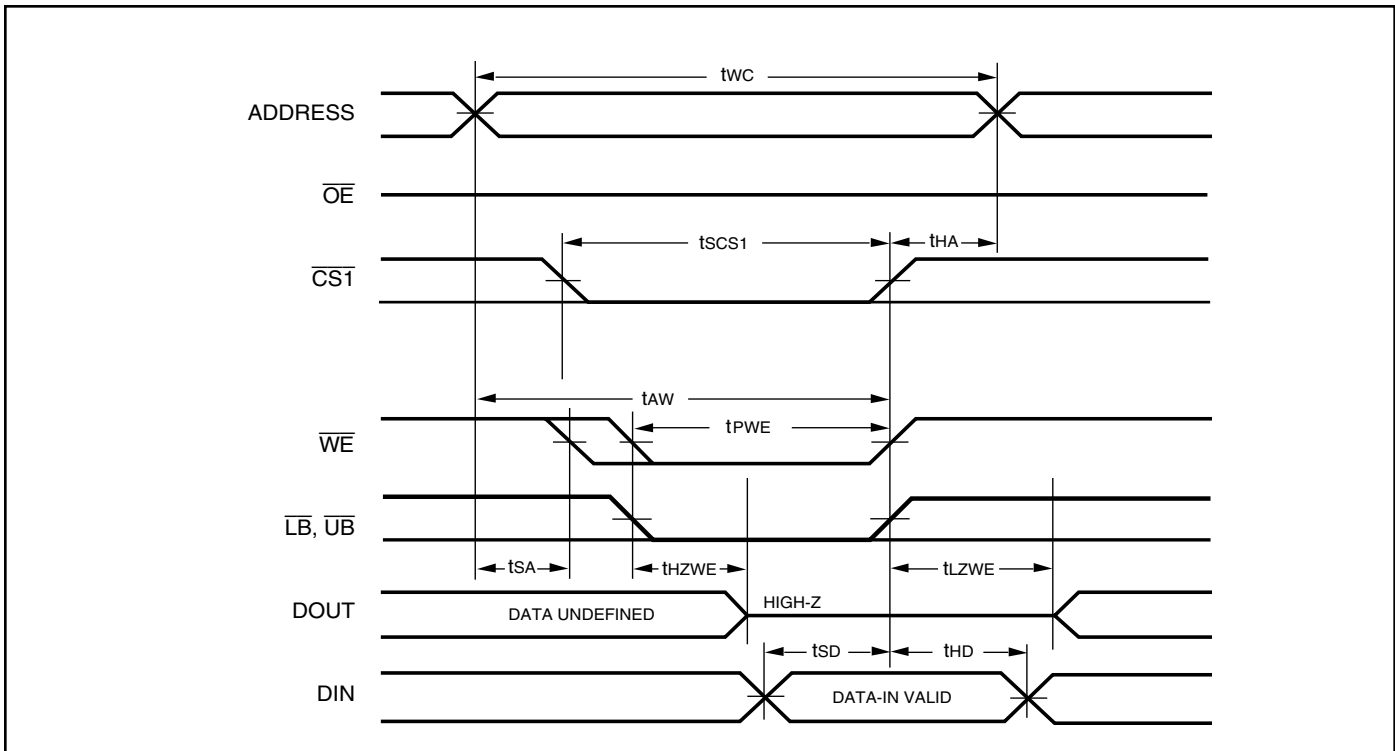
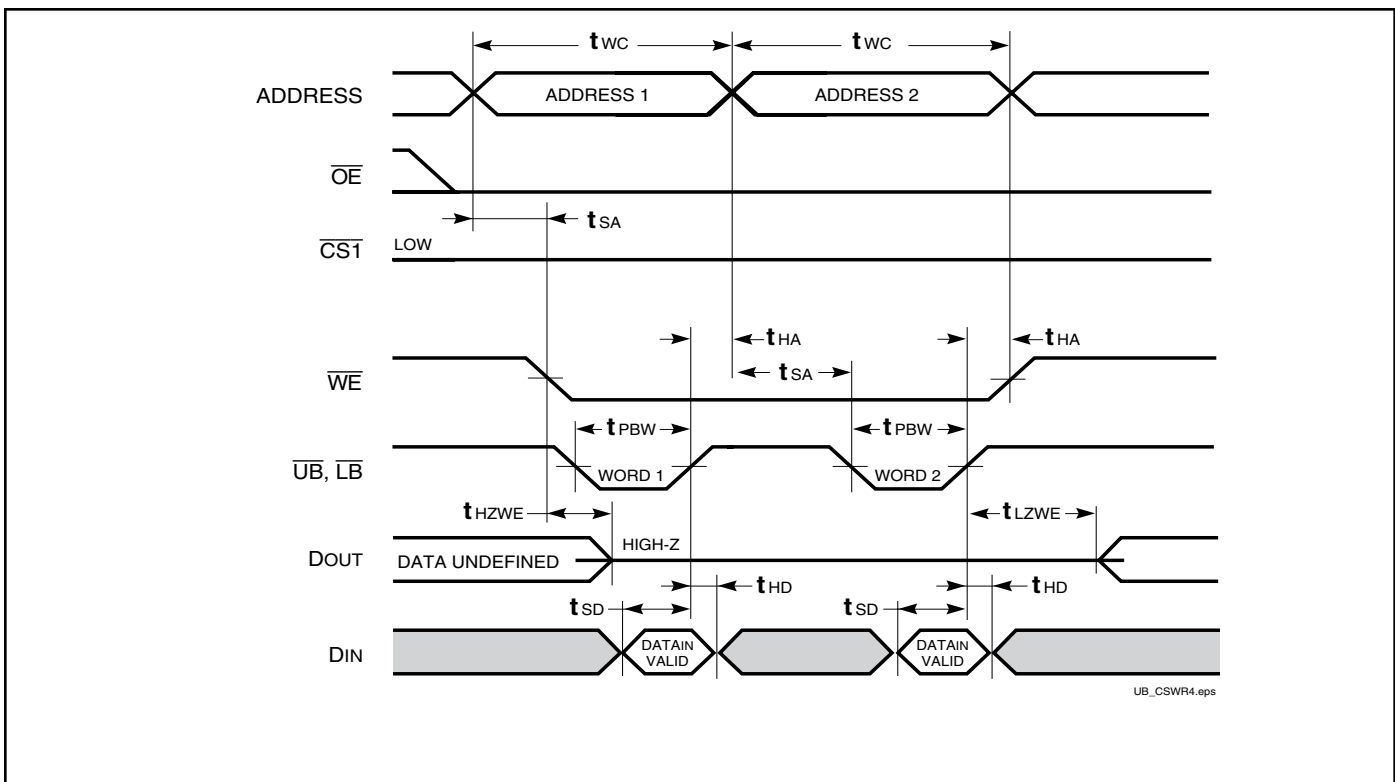


Notes:

1. WRITE is an internally generated signal asserted during an overlap of the LOW states on the $\overline{CS1}$ and $\overline{WE}$ inputs and at least one of the $\overline{LB}$ and $\overline{UB}$ inputs being in the LOW state.
2. WRITE = ($\overline{CS1}$) [($\overline{LB}$) = ($\overline{UB}$)] ($\overline{WE}$).

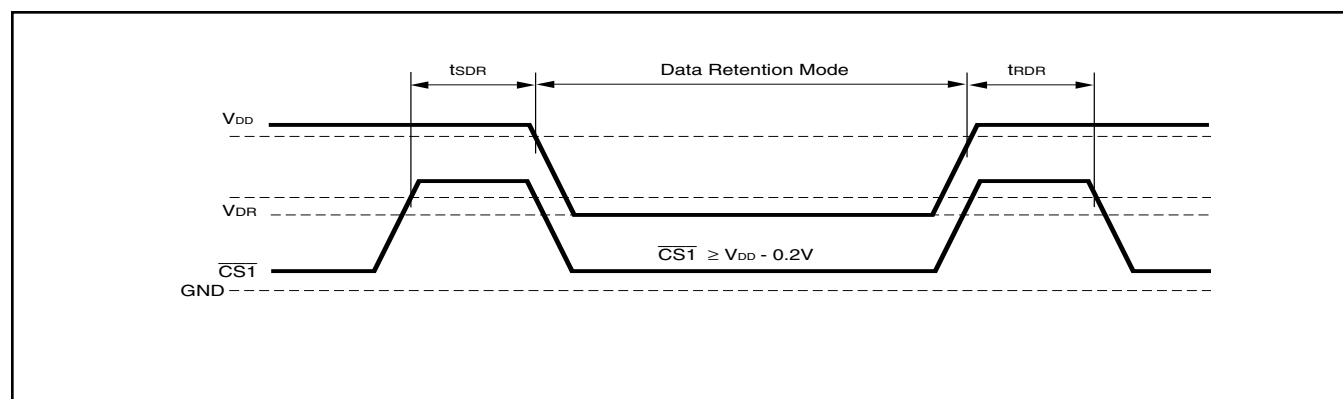
WRITE CYCLE NO. 2 ($\overline{WE}$ Controlled: $\overline{OE}$ is HIGH During Write Cycle)



WRITE CYCLE NO. 3 ($\overline{WE}$ Controlled: $\overline{OE}$ is LOW During Write Cycle)

WRITE CYCLE NO. 4 ($\overline{UB}/\overline{LB}$ Controlled)


DATA RETENTION SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition	Min.	Max.	Unit
V _{DR}	V _{DD} for Data Retention	See Data Retention Waveform	1.2	3.6	V
I _{DR}	Data Retention Current	V _{DD} = 1.2V, $\overline{CS1} \geq V_{DD} - 0.2V$	—	15	μA
t _{SDR}	Data Retention Setup Time	See Data Retention Waveform	0	—	ns
t _{RDR}	Recovery Time	See Data Retention Waveform	t _{RC}	—	ns

DATA RETENTION WAVEFORM ($\overline{CS1}$ Controlled)


IS62WV25616ALL, IS62WV25616BLL

ORDERING INFORMATION

IS62WV25616ALL (1.65V-2.2V)

Commercial Range: 0°C to +70°C

Speed (ns)	Order Part No.	Package
70	IS62WV25616ALL-70T	TSOP

Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
70	IS62WV25616ALL-70TI	TSOP
70	IS62WV25616ALL-70BI	mini BGA (6mmx8mm)
70	IS62WV25616ALL-70BLI	mini BGA (6mmx8mm), Lead-free

IS62WV25616BLL (2.5V - 3.6V)

Commercial Range: 0°C to +70°C

Speed (ns)	Order Part No.	Package
55	IS62WV25616BLL-55T	TSOP
70	IS62WV25616BLL-70T	TSOP

Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
55	IS62WV25616BLL-55TI	TSOP
55	IS62WV25616BLL-55TLI	TSOP, Lead-free
55	IS62WV25616BLL-55T2LI	TSOP, Lead-free, 2 CS Option
55	IS62WV25616BLL-55BI	mini BGA (6mmx8mm)
55	IS62WV25616BLL-55BLI	mini BGA (6mmx8mm), Lead-free

